

# FJP5021

## High Voltage and High Reliability

- High Speed Switching :  $t_F = 0.1\mu s$  (Typ.)
- Wide SOA



TO-220  
1.Base 2.Collector 3.Emitter

## NPN Silicon Transistor

### Absolute Maximum Ratings $T_C=25^\circ C$ unless otherwise noted

Symbol	Parameter	Value	Units
$V_{CBO}$	Collector-Base Voltage	800	V
$V_{CEO}$	Collector-Emitter Voltage	500	V
$V_{EBO}$	Emitter-Base Voltage	7	V
$I_C$	Collector Current (DC)	5	A
$I_{CP}$	Collector Current (Pulse)	10	A
$I_B$	Base Current	2	A
$P_C$	Collector Dissipation ( $T_C=25^\circ C$ )	50	W
$T_J$	Junction Temperature	150	$^\circ C$
$T_{STG}$	Storage Temperature	- 55 ~ 150	$^\circ C$

### Electrical Characteristics $T_C=25^\circ C$ unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
$BV_{CBO}$	Collector-Base Breakdown Voltage	$I_C = 1mA, I_E = 0$	800			V
$BV_{CEO}$	Collector-Emitter Breakdown Voltage	$I_C = 5mA, I_B = 0$	500			V
$BV_{EBO}$	Emitter-Base Breakdown Voltage	$I_E = 1mA, I_C = 0$	7			V
$V_{CEX(sus)}$	Collector-Emitter Sustaining Voltage	$I_C = 2.5A, I_{B1} = -I_{B2} = 1A$ $L = 1mH, \text{Clamped}$	500			V
$I_{CBO}$	Collector Cut-off Current	$V_{CB} = 500V, I_E = 0$			10	$\mu A$
$I_{EBO}$	Emitter Cut-off Current	$V_{EB} = 5V, I_C = 0$			10	$\mu A$
$h_{FE1}$ $h_{FE2}$	DC Current Gain	$V_{CE} = 5V, I_C = 0.6A$ $V_{CE} = 5V, I_C = 3A$	15 8		50	
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = 3A, I_B = 0.6A$			1	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C = 3A, I_B = 0.6A$			1.5	V
$C_{ob}$	Output Capacitance	$V_{CB} = 10V, I_E = 0, f=1MHz$		80		pF
$f_T$	Current Gain Bandwidth Product	$V_{CE} = 10V, I_C = 0.6A$		18		MHz
$t_{ON}$	Turn On Time	$V_{CC} = 200V$			0.5	$\mu s$
$t_{STG}$	Storage Time	$I_C = 5I_{B1} = -2.5I_{B2} = 4A$			3	$\mu s$
$t_F$	Fall Time	$R_L = 50\Omega$		0.1	0.3	$\mu s$

### $h_{FE}$ Classification

Classification	R	O	Y
$h_{FE1}$	15 ~ 30	20 ~ 40	30 ~ 50

# Typical Characteristics

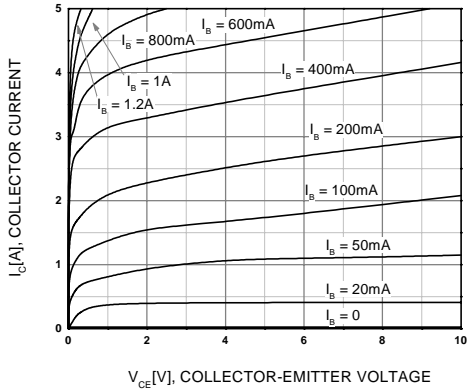


Figure 1. Static Characteristic

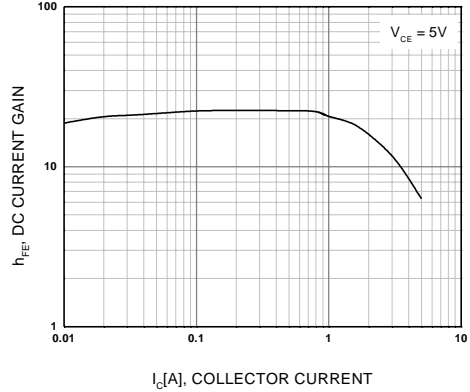


Figure 2. DC current Gain

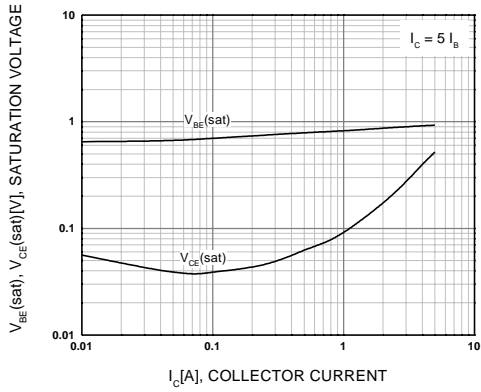


Figure 3. Base-Emitter Saturation Voltage  
Collector-Emitter Saturation Voltage

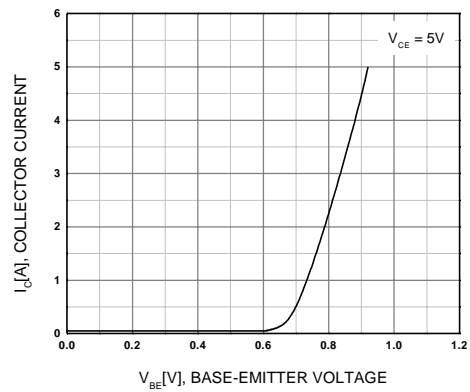


Figure 4. Base-Emitter On Voltage

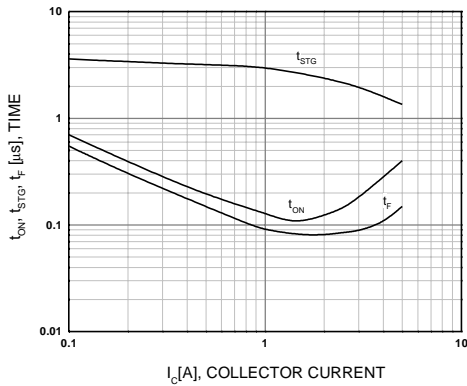


Figure 5. Switching Time

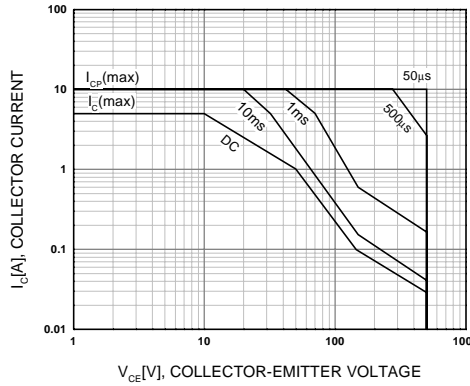


Figure 6. Forward Bias Safe Operating Area

Typical Characteristics (Continued)

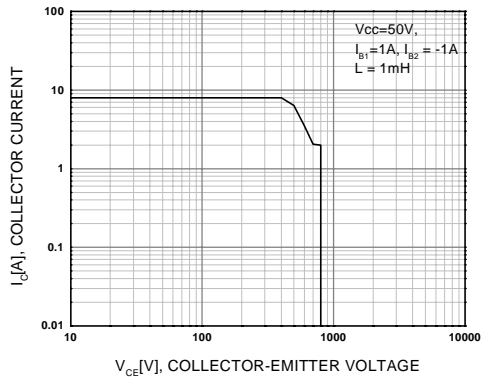


Figure 7. Reverse Bias Safe Operating Area

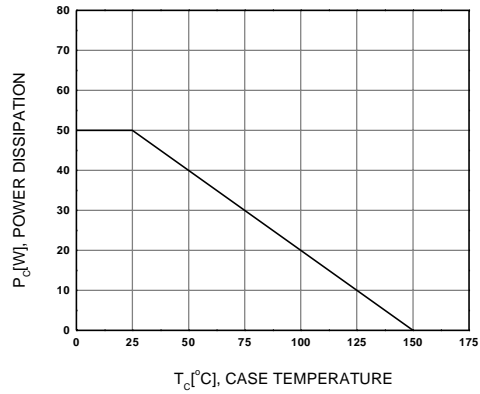
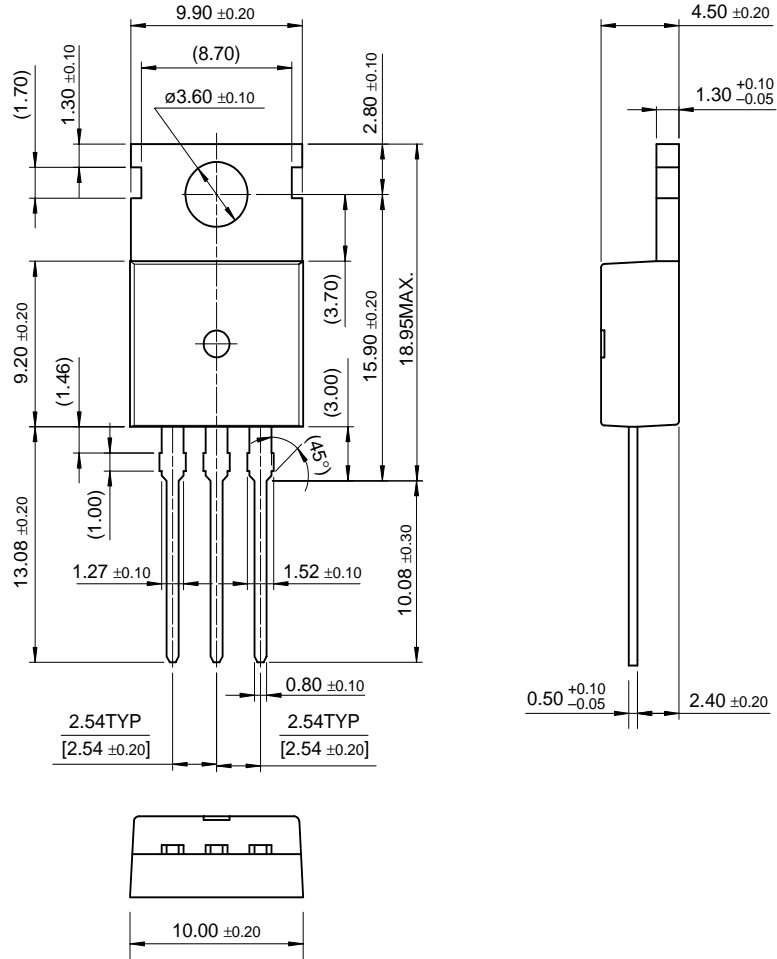


Figure 8. Power Derating

Package Dimensions

TO-220



Dimensions in Millimeters

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